Hologram Lasers GH6CD05B3A

# GH6CD05B3A

# (Under development)

#### ■ Features

- With built-in 3V operation(3 to 5V), ×8 speed playback OPIC\*
- Reducing variety of offset voltage (40% reduction) enables easy compatibility with CD-RW media.
- (3) Insert frame structure enables easy mounting compared to conventional pin structure.
- (4) Thin(4.8mm thickness) and compact package enables thin and compact pick-up design.
- (5) With built-in beam splitter and diffraction grating \*OPIC: (Optical IC) is a trademark of SHARP Corporation. An OPIC consists of a light-detecting element and a signal-processing circuit integrated onto a single chip.

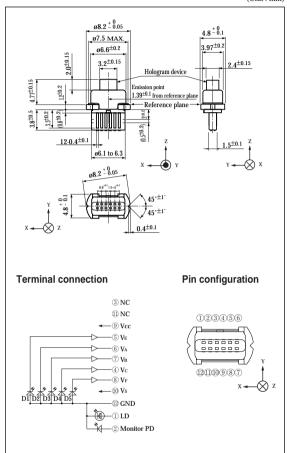
# ■ Applications

- (1) CD audio players
- (2) Video CD players

# 4.8mm Thickness Resin Stem Hologram Laser for CD Audio/Video CD Drive

#### Outline Dimensions

(Unit : mm)



#### ■ Absolute Maximum Ratings

	Parame	eter	Symbol	Rating	Unit
#1	Optical power output	Рн	4.3	mW	
	Reverse voltage	Laser	V <sub>R</sub>	2	V
		Monitor photodiode	VR	30	V
	OPIC supply voltag	Vcc	6	V	
#2	Operating temperat	Topr	-10 to +70	°C	
*2	Storage temperatur	Tstg	-40 to +85	°C	
#3	Soldering temperat	ure	Tsold	260	°C

<sup>\*1</sup> Output power from hologram laser, CW (Continuous Wave) drive

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 $(Tc=25^{\circ}C)$ 

<sup>\*2</sup> Case temperature

<sup>\*3</sup> At the position of 0.5mm from the lead base (Within 5s)

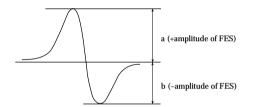
# **■** Electro-optical Characteristics

(Vcc=5V,Vs=1/2 Vcc, Tc=25°C)

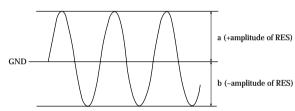
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
*1 Focal offset	DEF	V <sub>RF</sub> =1.1V	-0.7	-	+0.7	μm
*2 Focal error symmetry	Bres	V <sub>RF</sub> =1.1V	-25	-	+25	%
*3 Radial error balance	Bres	P <sub>H</sub> =3.0mW	-25	-	+25	%
**4 RF output amplitude	Vrf	Рн=3.0mW	0.9	(1.7)	-	V
*5 FES output amplitude	VFES	V <sub>RF</sub> =1.1V	0.46	(0.7)	0.94	V
*6 RES output amplitude	Vres	Vrf=1.1V	0.25	(0.36)	0.49	V
Threshold current	Ith	_	-	(25)	39	mA
Operating current	Iop	P <sub>H</sub> =3.0mW	-	(36)	50	mA
Operating voltage	Vop	P <sub>H</sub> =3.0mW	-	(1.85)	2.2	V
Wavelength	$\lambda_{\mathrm{p}}$	Рн=3.0mW	770	(780)	795	nm
Output current	Im	P <sub>H</sub> =3.0mW, V <sub>R</sub> =15V	0.06	(0.32)	0.60	mA
Differential efficiency	ηα	2.0mW I(3.0mW)-I(1.0mW)	0.17	(0.27)	0.55	mW/mA

 $<sup>^{*1}</sup>$  Distance between FES=0 and jitter minimum point At the condition of FES sensitivity =  $20\%/1\mu m$ 

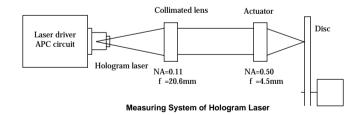
<sup>\*2 (</sup>a-b) / (a+b)







- \*\*4 Amplitude of Va+VB+2Vc (focal servo ON, radial servo ON)
- \*5 V<sub>A</sub>–V<sub>B</sub> (focal vibration)
- \*6 VE-VF (focal servo ON, radial servo OFF)

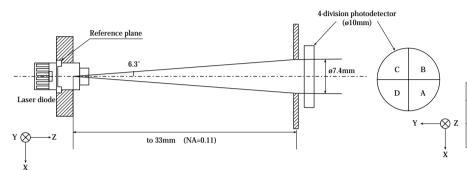


# Electro-optical Characteristics of Laser Diode (Design Standard\*)

 $(Tc=25^{\circ}C)$ 

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Emission	*1 Symmetry Parallel Perpendicular	S//	D- 2W I NA 0.11	-25	-	+25	%	
characteristics		Perpendicular	S⊥	Po=3mW, Into NA=0.11	-15	-	+15	%
Misalignment position			$\Delta \mathbf{x}$	_	-80	-	+80	μm
			$\Delta y$		-80	-	+80	μm
		$\Delta z$	-80		-	+80	μm	
Z - position of emission point		z	_	-	1.39	-	mm	
Interference pattern intensity			α	Po=3mW	-	-	0.99	-

Measuring method of radiation symmetry



Parameter	Definition
S//	$\frac{(P_{\rm B} + P_{\rm C}) - (P_{\rm A} + P_{\rm D})}{P_{\rm A} + P_{\rm B} + P_{\rm C} + P_{\rm D}}$
s⊥	$\frac{(P_A + P_B) - (P_C + P_D)}{P_A + P_B + P_C + P_D}$

Px: Output of light detector X

### Electrical Characteristics of Monitor Photodiode (Design Standard\*)

 $(Tc=25^{\circ}C)$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
*2 Sensitivity	S		-	0.11	-	mA/mW
Dark current	ID	V <sub>R</sub> =15V	-	-	150	nA
Terminal capacitance	Ct		-	4.2	-	pF

For hologram output power

D5

# Electro-optical Characteristics of OPIC for Signal Detection (Design Standard\*)

 $(Tc=25^{\circ}C)$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	*3 Segment
Supply voltage	Vcc		2.8	3	5.5	V	
Supply current	Icc	Vcc=3V	6	9	12	mA	
**4 Output offset voltage	Vod		-15	0	+15	mV	Va, Vb, Vc
Output onset voltage		Vcc=3V	-17	0	+17	mV	Ve, Vf
Offset valtage difference	$\Delta V$ od	No light	-15	0	+15	mV	Va-VB
Offset voltage difference			-17	0	+17	mV	VE-VF
D	fcF	*5 Vcc=3V, -3dB	12	18	-	MHz	Va, Vb, Vc
Response frequency	fcr	RL=10kΩ, CL=10pF	1.2	1.8	-	MHz	Ve, Vf

<sup>\*3</sup> Applicable divisions correspond to output terminals.

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<sup>\*4</sup> Difference from Vs

Segment No. Output D1 D 1 ......VE D2D 2 ......VA D4 D3D 3 ......V<sub>B</sub> D 4 ......Vc

D 5 ......VF

Output amplitude=0dB (input signal 100kHz) BW=10kHz

<sup>\*</sup> These parameters are not guaranteed performance, but general specifications of each optical element which makes up a hologram laser.

<sup>·</sup> Please refer to the chapter "Handling Precautions"

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